

<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>				Complete if Known <b>10/574512</b>	
				Application Number	New Application
				Filing Date	April 3, 2006
				First Named Inventor	MASSELINK et al
				Group Art Unit	2815
				Examiner Name	Ho, Anthony
				Confirmation No.	
Sheet	1	of	3	Attorney Docket Number	3367-102

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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published		T <sup>2</sup>
/A.H./	4.	W. T. Masselink and Yia-Chung Chang, "Theory of the Exciton Bound to an Isoelectronic Trap in GaP," Phys. Rev. Lett. 51, 509-512 (1983)		
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/A.H./	10.	W. T. Masselink, F. Hatami, G. Mussler, and L. Schrottke: "InP quantum dots in (100) GaP: Growth and luminescence", Materials Science in Semi-conductor Processing 4, 497-501 (2001) (Proceedings of the International Conference on Materials for Advanced Technologies (ICMAT 2001), 1-6 July 2001, Singapore)		
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Examiner Signature	/Anthony Ho/	Date Considered	08/21/2007
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